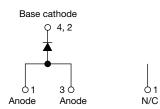
### VS-15AWL06FN-M3, VS-15EWL06FN-M3

Vishay Semiconductors

## Ultralow V<sub>F</sub> Ultrafast Rectifier, 15 A FRED Pt®



#### DPAK (TO-252AA)





VS-15EWL06FN-M3

PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	15 A					
V <sub>R</sub>	600 V					
V <sub>F</sub> at I <sub>F</sub>	0.85 V					
t <sub>rr</sub> (typ.)	60 ns					
T <sub>J</sub> max.	175 °C					
Package	DPAK (TO-252AA)					
Circuit configuration	Single					

#### **FEATURES**

 Ultrafast recovery time, extremely low V<sub>F</sub> and soft recovery



• 175 °C maximum operating junction temperature

• For PFC DCM operation

COMPLIANT HALOGEN FREE

- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art, ultralow  $V_F$ , soft-switching hyperfast rectifiers optimized for Discontinuous (Critical) Mode (DCM) Power Factor Correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	$V_{RRM}$		600	V			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 148 °C	15				
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	180	Α			
Peak repetitive forward current	I <sub>FM</sub>	T <sub>C</sub> = 148 °C, f = 20 kHz, d = 50 %	30				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-	.,		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	0.99	1.05	V		
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	0.85	0.92			
Poverse leakage ourrent	I <sub>R</sub>	$V_R = V_R$ rated	-	-	10			
Reverse leakage current		$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$		120	μΑ			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	11	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V <sub>R</sub> = 30 V	-	60	120		
Reverse recovery time	t <sub>rr</sub>	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	190	-		
		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	-	220	-	ns	
		T <sub>J</sub> = 125 °C		-	290	-		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	21	-	Α	
		T <sub>J</sub> = 125 °C		-	25	-		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	2.6	-		
		T <sub>J</sub> = 125 °C		-	4	-	μC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	1.4	1.8	°C/W		
Thermal resistance, junction to ambient	R <sub>thJA</sub>		-	-	70	C/VV		
Approximate weight				0.3		g		
Approximate weight				0.01		OZ.		
Madina desire		Consist to BRAK (TO SERAA)			L06FN			
Marking device		Case style DPAK (TO-252AA)	15EWL06FN					

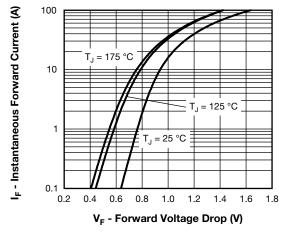


Fig. 1 - Typical Forward Voltage Drop Characteristics

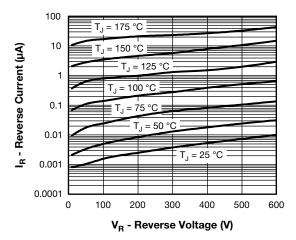


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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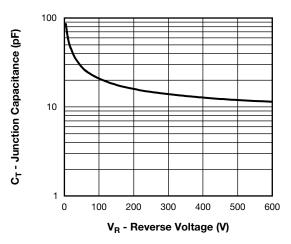


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

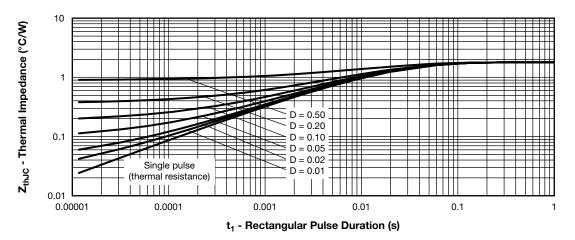


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

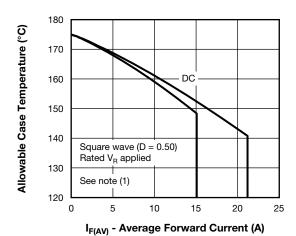


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

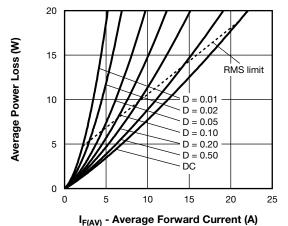


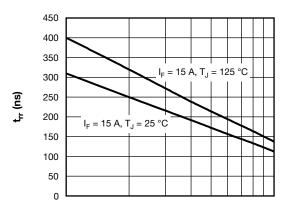
Fig. 6 - Forward Power Loss Characteristics

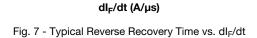
#### Note

Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>th,JC</sub>; Pd = forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>

100

### Vishay Semiconductors





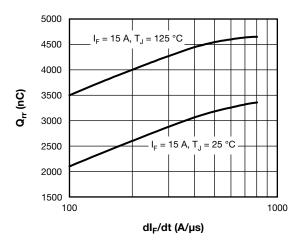
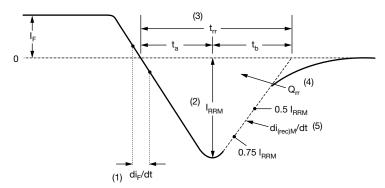


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current

1000

- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\rm Q_{rr}$  area under curve defined by  $\rm t_{rr}$  and  $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

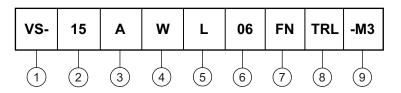
Fig. 9 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (15 = 15 A)

3 - Circuit configuration:

• A = single diode (2 anodes)

• E = single diode

4 - Package identifier:

W = DPAK

5 - L = hyperfast rectifier

6 - Voltage rating (06 = 600 V)

7 - FN = TO-252AA

8 - • None = tube

• TR = tape and reel

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-15AWL06FN-M3	75	Antistatio plantic tub o					
VS-15EWL06FN-M3	75	Antistatic plastic tube					
VS-15AWL06FNTR-M3	2000	13" diameter reel					
VS-15EWL06FNTR-M3	2000	13 diameter reel					
VS-15AWL06FNTRL-M3	3000	13" diameter reel					
VS-15EWL06FNTRL-M3	3000	13 diameter reer					
VS-15AWL06FNTRR-M3	3000	13" diameter reel					
VS-15EWL06FNTRR-M3	3000	13 diameter reei					

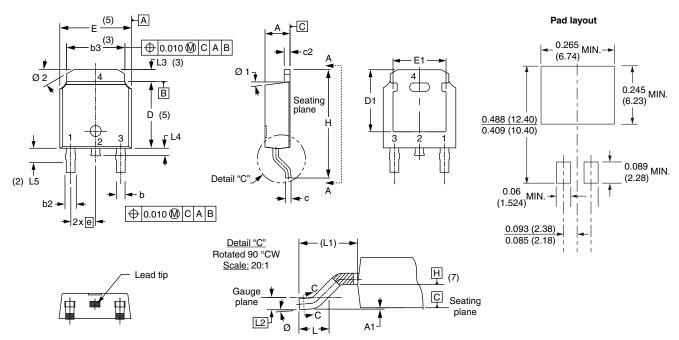
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95627					
Part marking information	www.vishay.com/doc?95176					
Packaging information	www.vishay.com/doc?95033					
SPICE model	www.vishay.com/doc?95372					



### Vishay Semiconductors

## D-PAK (TO-252AA) "M"

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	SY
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	31
Α	2.18	2.39	0.086	0.094		
A1	-	0.13	-	0.005		
b	0.64	0.89	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215	3	
С	0.46	0.61	0.018	0.024		
c2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245	5	
D1	5.21	-	0.205	-	3	
Е	6.35	6.73	0.250	0.265	5	
E1	4.32	-	0.170	-	3	

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29	BSC	0.090	BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51	BSC	0.020 BSC		
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0°	10°	
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC® outline TO-252AA



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